

TO-126 Plastic-Encapsulate Transistors

3DA882 TRANSISTOR (NPN)

FEATURES

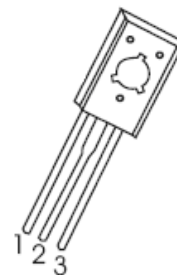
- Low Speed Switching
- Complement to 3CA772

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

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1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			10	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{V}, I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			10	μA
DC current gain	h_{FE}^*	$V_{CE}=2\text{V}, I_C=1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=2\text{A}, I_B=0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=0.1\text{A}, f=10\text{MHz}$	50			MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 2.0\%$.

CLASSIFICATION OF h_{FE}

RANK	R	O	Y	GR
RANGE	60-120	100-200	160-320	200-400